

FIG.1

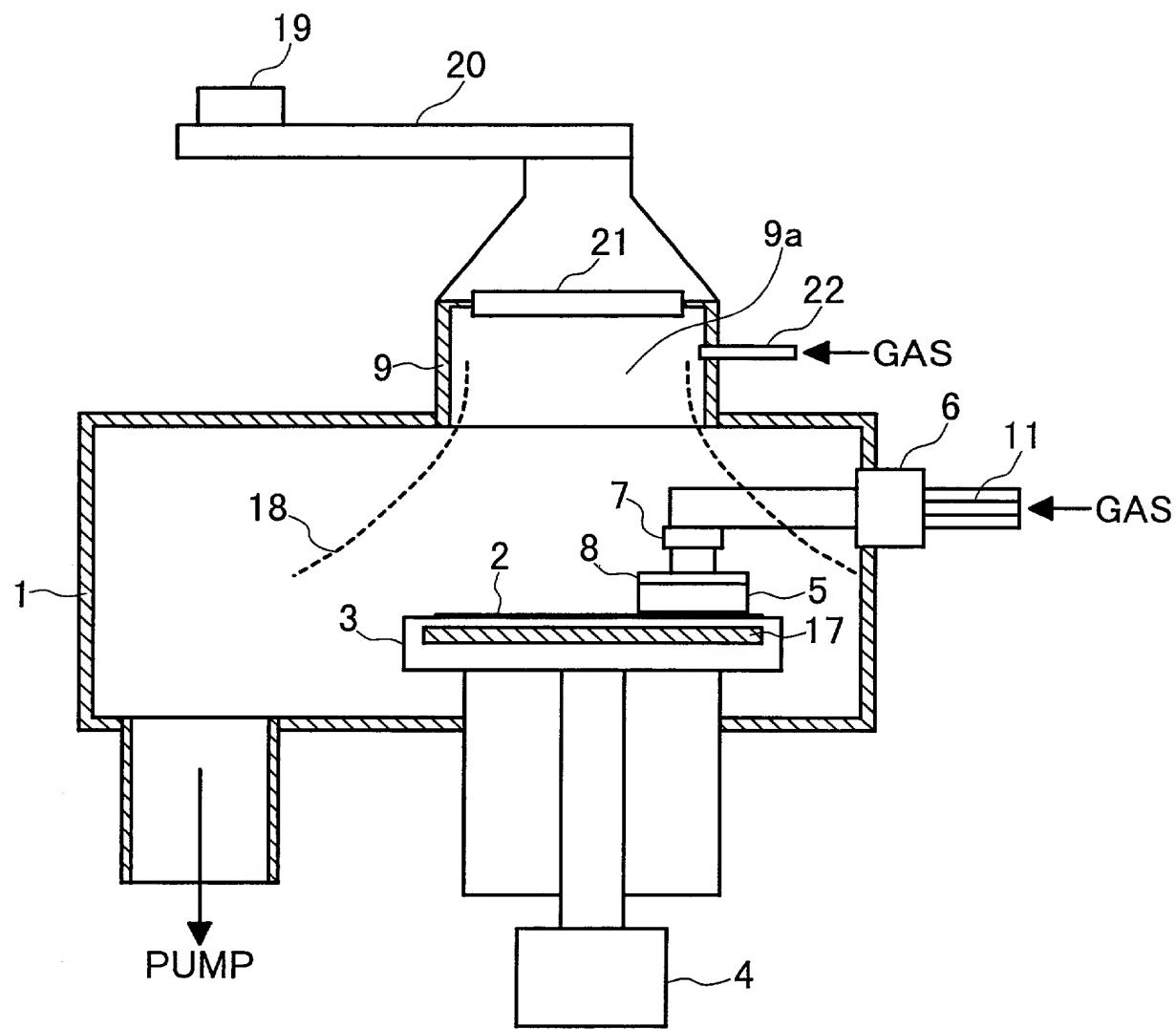


FIG.2

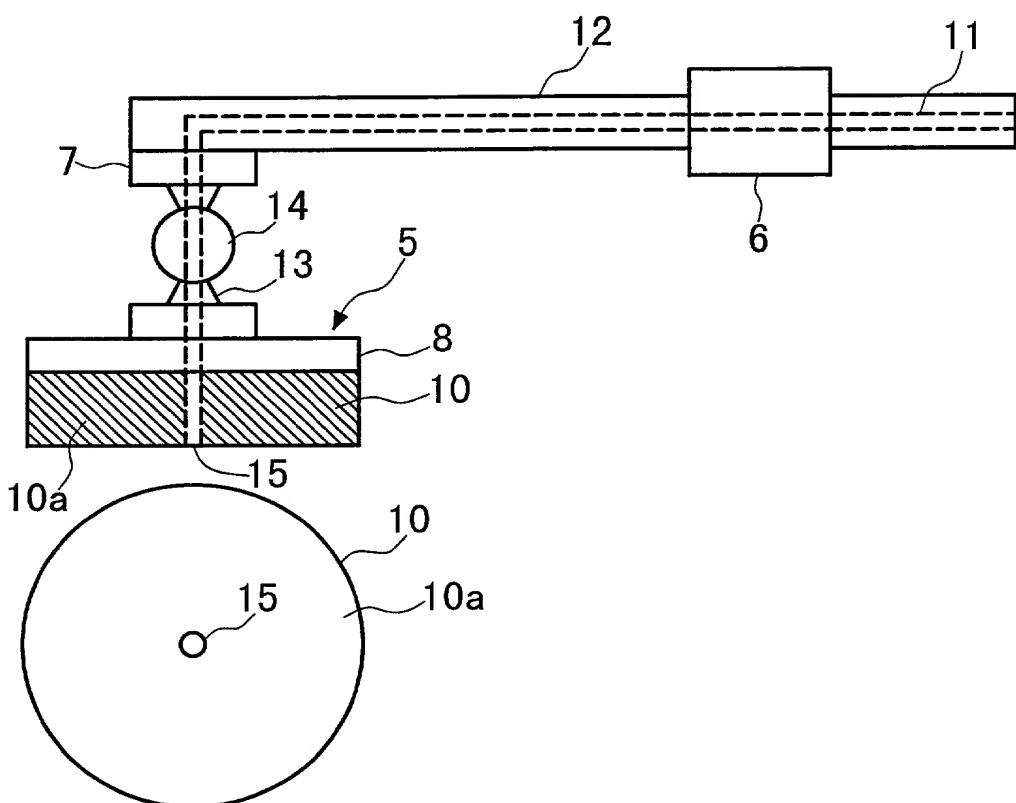


FIG.3

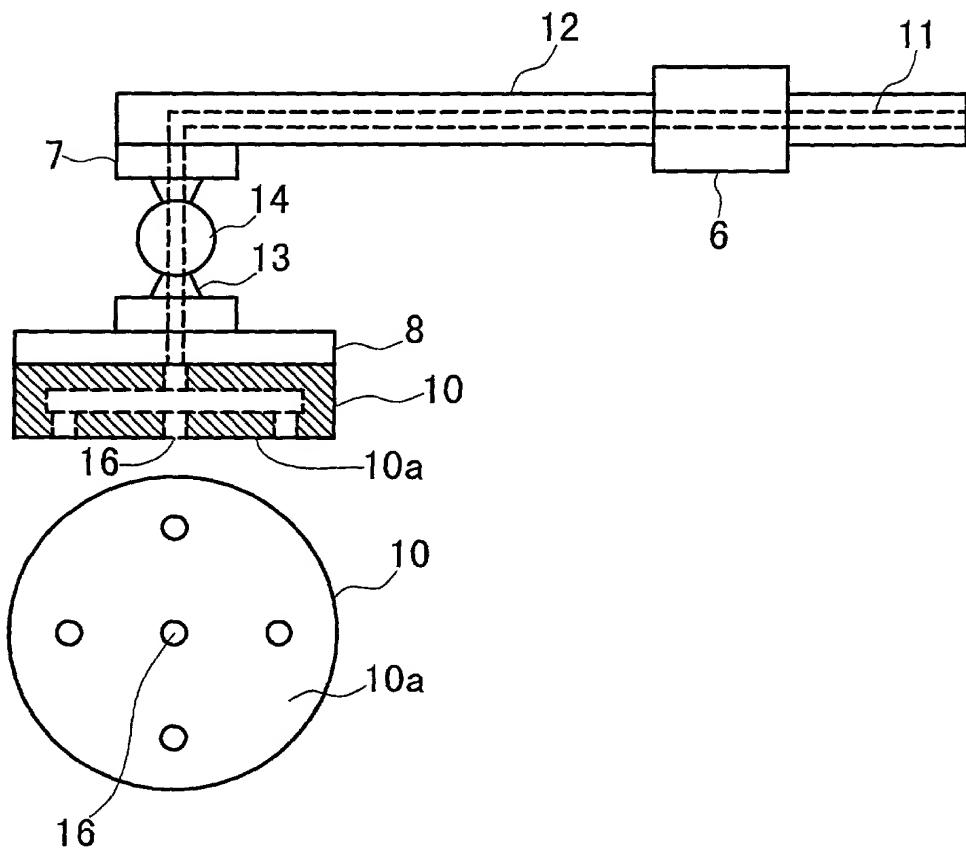
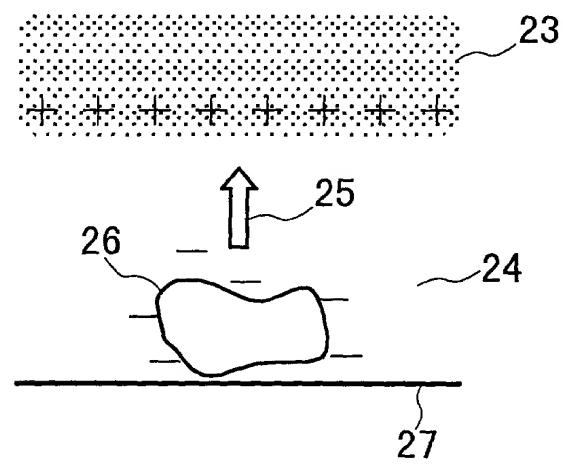
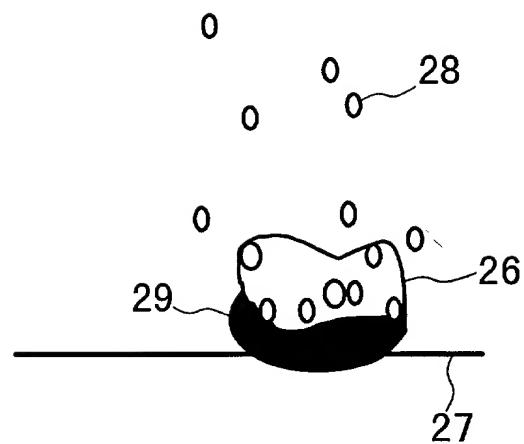
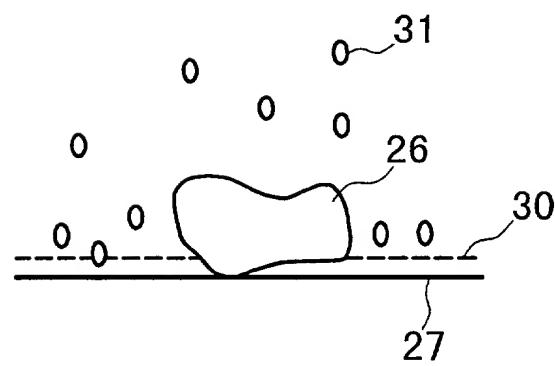
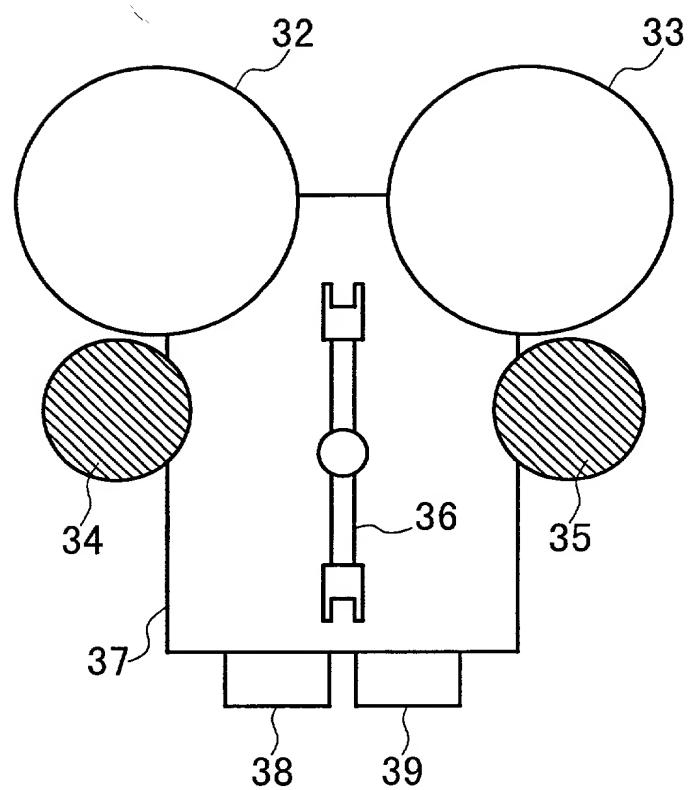


FIG.4



**FIG.5****FIG.6**

**FIG.7**

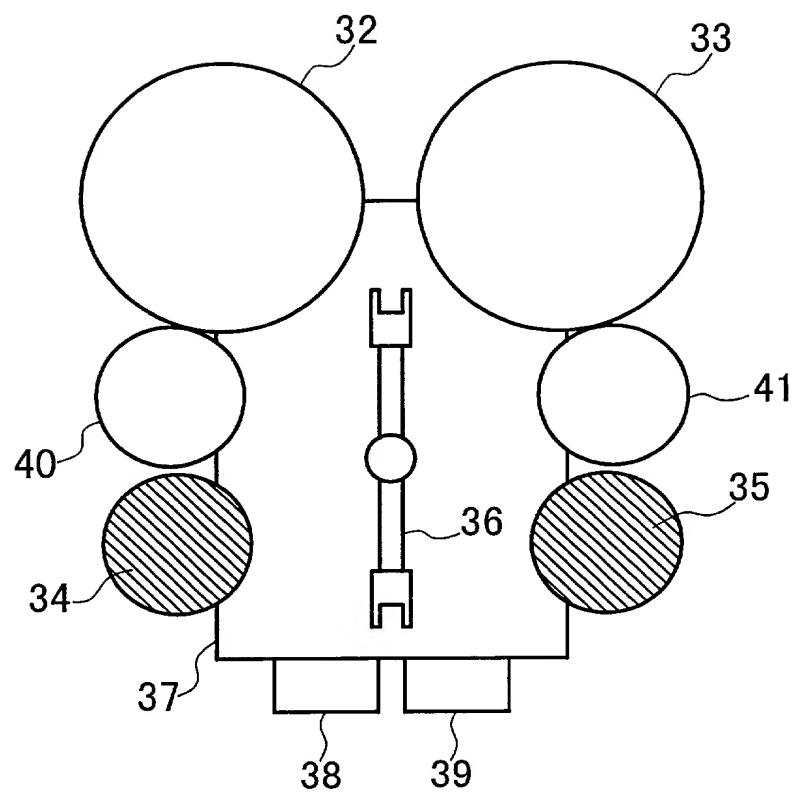
**FIG.8**

FIG.9

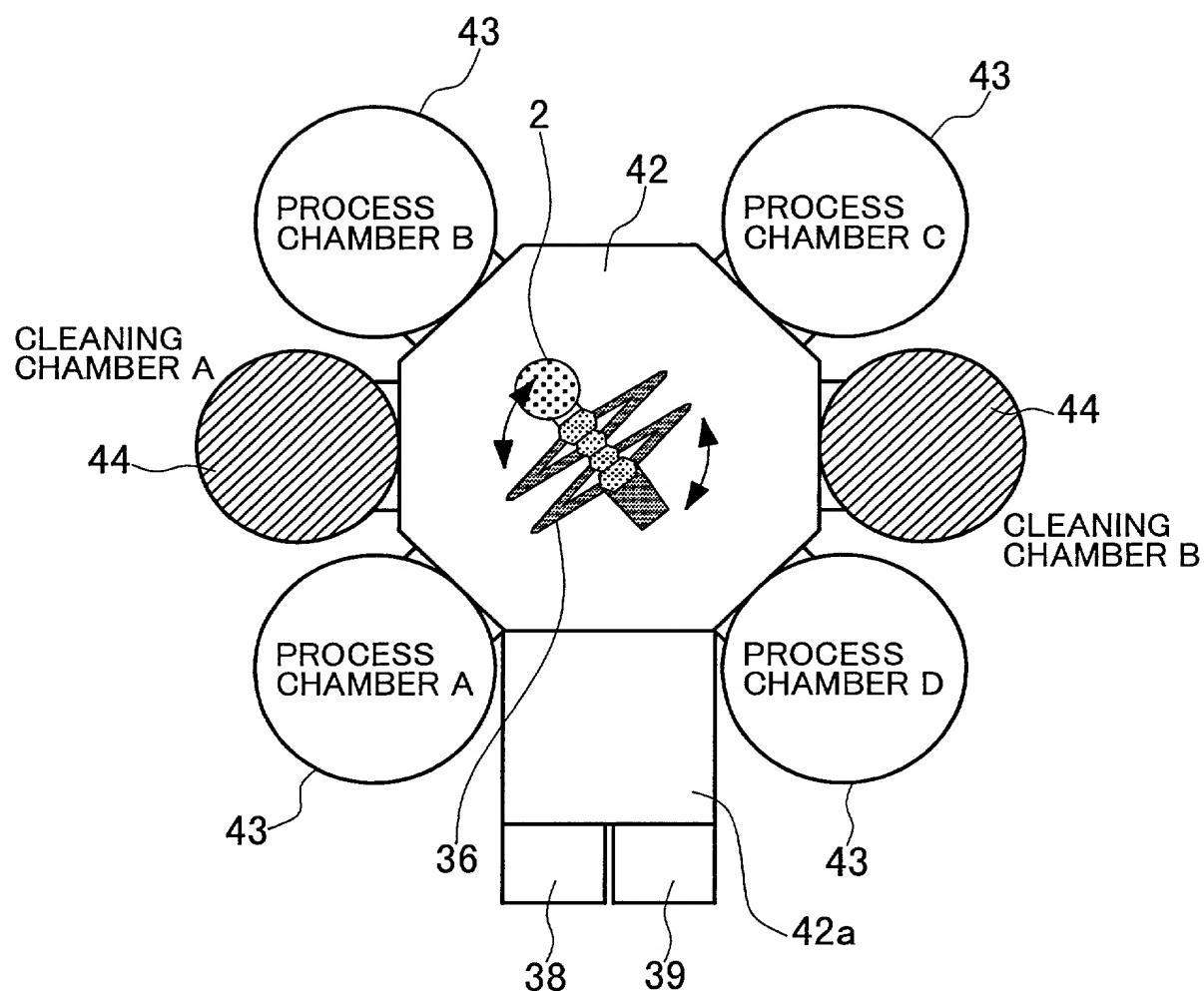


FIG.10A

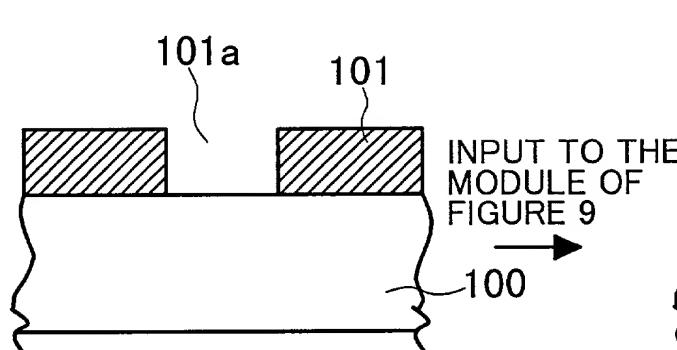


FIG.10B

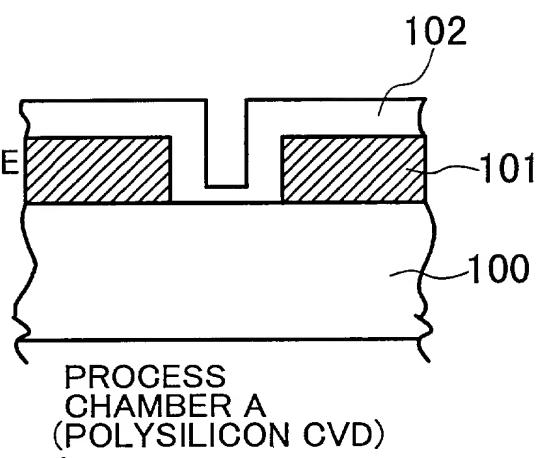


FIG.10C (CLEANING CHAMBER A)

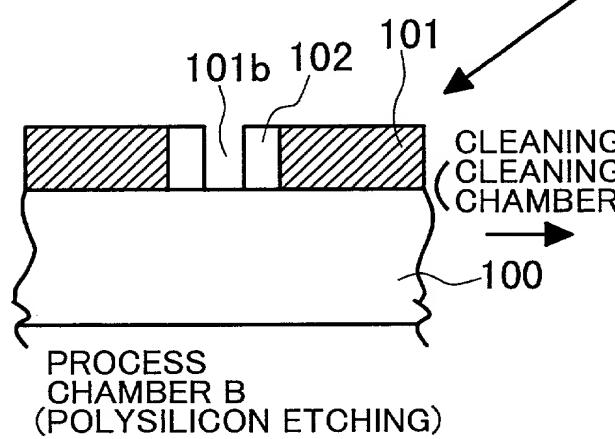


FIG.10D

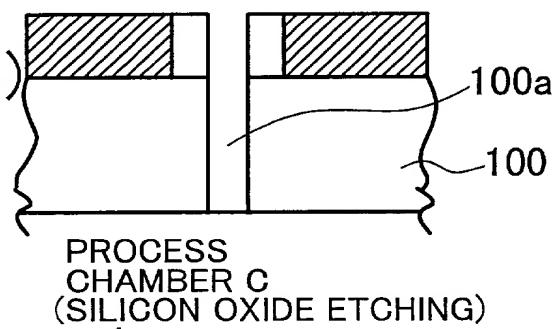
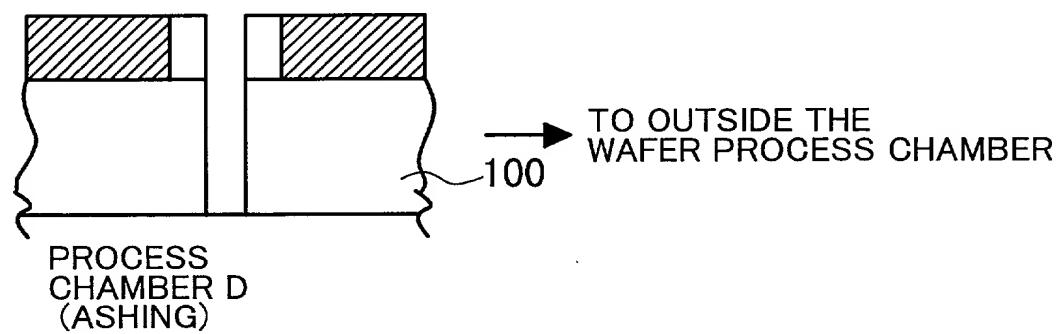


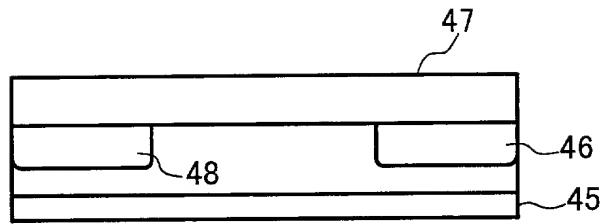
FIG.10E



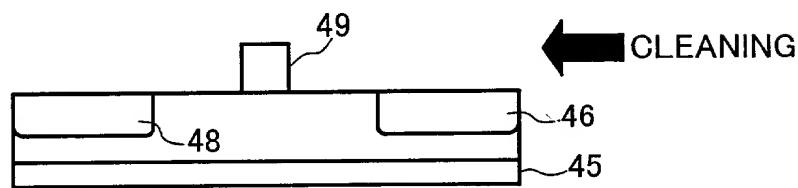
PROCESS CHAMBER D (ASHING)

**FIG.11A**

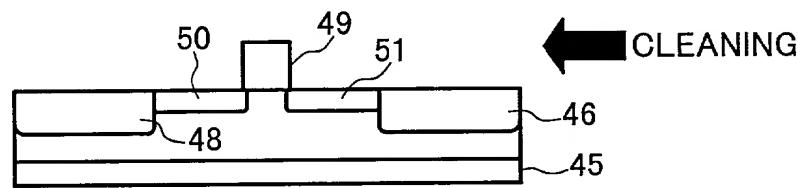
FABRICATION  
OF DEVICE ISOLATION  
REGION AND DEPOSITION  
OF POLYSILICON

**FIG.11B**

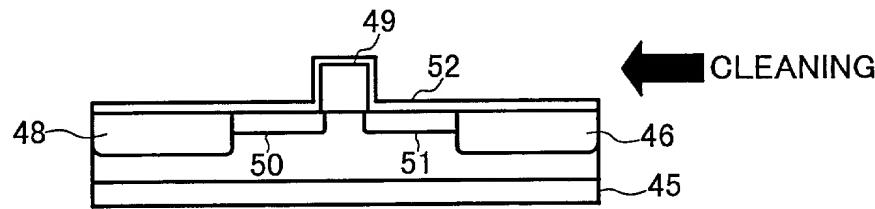
FABRICATION  
OF GATE ELECTRODE  
(POLYSILICON ETCHING)

**FIG.11C**

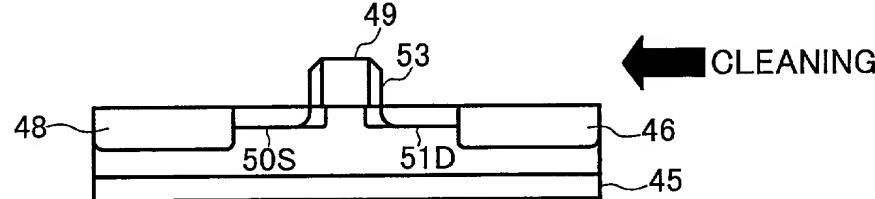
FABRICATION  
OF EXTENSION

**FIG.11D**

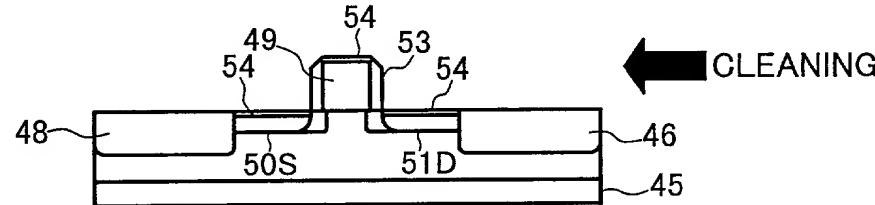
DEPOSITION  
OF NITRIDE FILM

**FIG.11E**

FABRICATION  
OF GATE SIDE  
WALL FILM

**FIG.11F**

FABRICATION  
OF SILISIDE



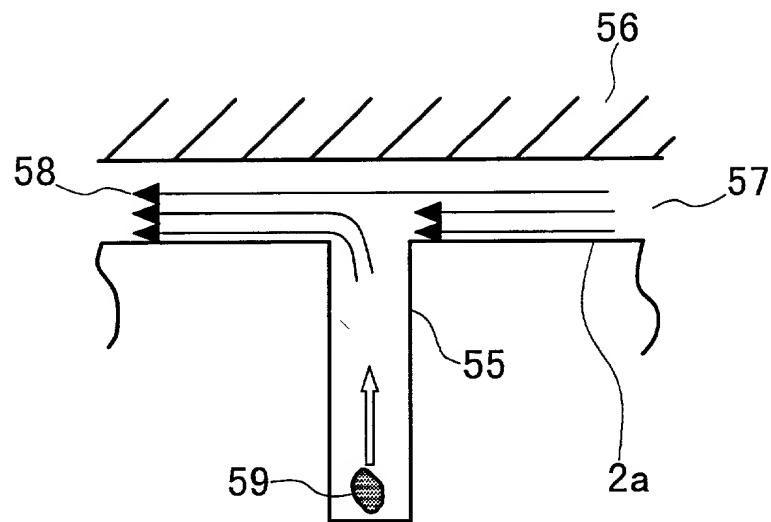
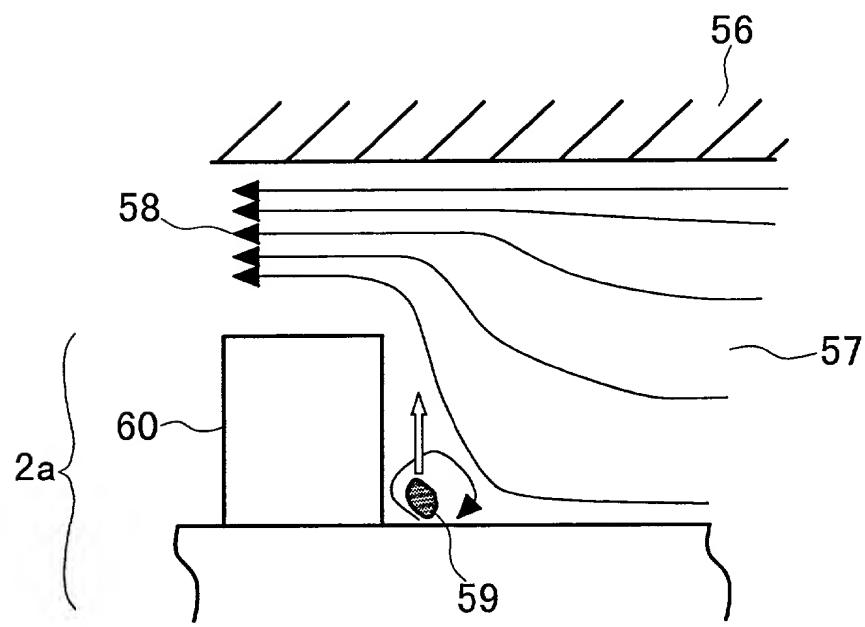
**FIG.12A****FIG.12B**

FIG.13

